



4x64Kx64, 3.3V Synchronous SRAM CARD EDGE DIMM

FEATURES

- 4x64Kx64 Synchronous
- Access Speed(s): $T_{KHQV} = 9.5, 10, 11, 12, 15\text{ns}$
- Flow-Through Architecture
- Clock Controlled Registered Bank Enables ($E1\backslash, E2\backslash, E3\backslash, E4\backslash$)
- Clock Controlled Registered Address
- Clock Controlled Registered Global Write (GW)
- Asynchronous Output Enable ($G\backslash$)
- Internally self-timed Write+
- Gold Lead Finish
- $3.3V \pm 10\%, -5\%$ Operation
- Common Data I/O
- High Capacitance (30pF) drive, at rated Access Speed
- Single total array Clock
- Multiple V_{cc} and V_{ss}

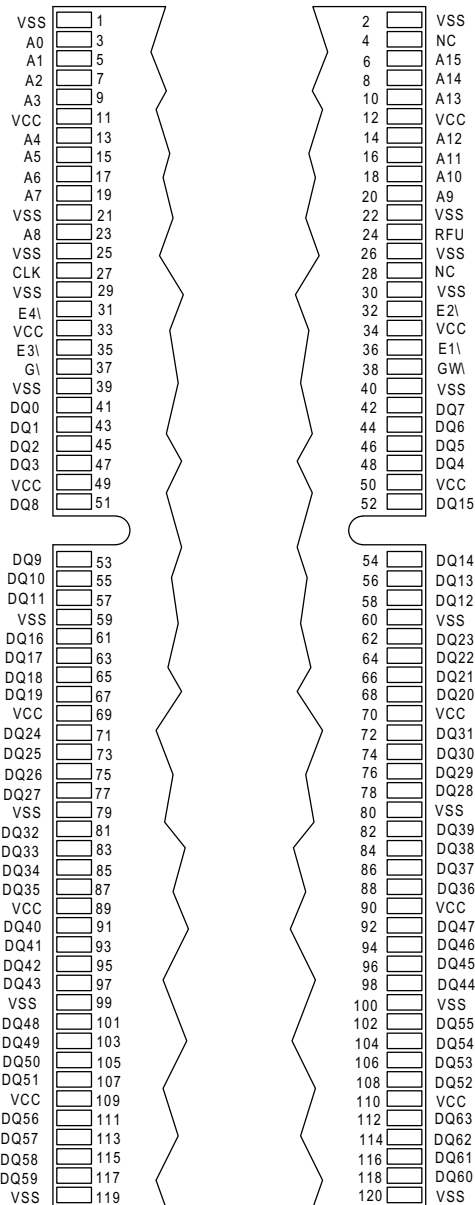
The EDI2GG46464VxxD is a Synchronous SRAM, 60 position Dual Key; Card Edge DIMM (120 contacts) Module, organized as 4x64Kx64. The Module contains eight (8) Synchronous Burst Ram Devices, packaged in the industry standard JEDEC 14mmx20mm TQFP placed on a Multilayer FR4 Substrate. The module architecture is defined as a Synchronous Only, Flow-Through, Early Write device. This Module provides high performance, ultra fast access times at a cost per bit benefit over BiCMOS Asynchronous devices. As well as improved cost per bit, the use of Synchronous or Synchronous burst devices or modules can ease the memory subsystem design by reducing or easing the memory controller requirement.

Synchronous operations are in relation to an externally supplied clock, registered address, registered global write, registered enables as well as an Asynchronous Output enable. All Read and Write operations are performed in Quad Words (64 bit operations).

Write cycles are internally self timed and are initiated by a rising clock edge. This feature relieves the designer the task of developing external pulse width circuitry.

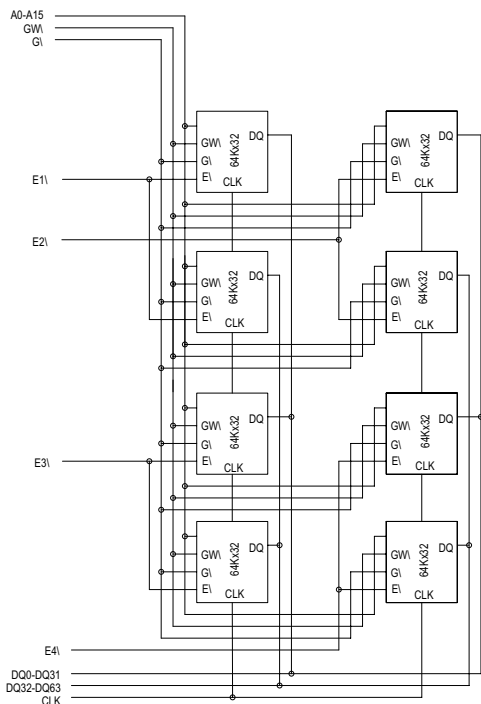


PIN CONFIGURATION





FUNCTIONAL BLOCK DIAGRAM



PIN NAMES

DQ0-63	Input/Output Bus
A0-15	Address Bus
E1\, E2\, E3\, E4\	Synchronous Bank Enables
CLK	Array Clock
GW\	Synchronous Global Write Enable
GI\	Asynchronous Output Enable
Vcc	3.3V Power Supply
Vss	Ground
NC	No Connect

PIN DESCRIPTIONS

DIMM Pins	Symbol	Type	Description
3, 5, 7, 9, 13, 15, 17, 19, 23, 20, 18, 16, 14, 10, 8, 6	A0-15	Input Synchronous	Addresses: These inputs are registered and must meet the setup and hold times around the rising edge of CLK. The burst counter generates internal addresses associated with A0 and A1, during burst and wait cycle.
38	GW\	Input Synchronous	Global Write: This active LOW input allows a full 72-bit WRITE to occur independent of the BWE\ and BWx\ lines and must meet the setup and hold times around the rising edge of CLK.
27	CLK	Input Synchronous	Clock: This signal registers the addresses, data, chip enables, write control and burst control inputs on its rising edge. All synchronous inputs must meet setup and hold times around the clock's rising edge.
36, 32, 35, 31	E1\, E2\ E3\, E4\	Input Synchronous	Bank Enables: These active LOW inputs are used to enable each individual bank and to gate ADSP\.
37	GI\	Input	Output Enable: This active LOW asynchronous input enables the data output drivers.
Various	DQ0-63	Input/Output	Data Inputs/Outputs: First byte is DQ0-7, second byte is DQ8-15, third byte is DQ16-23, fourth byte is DQ24-31, fifth byte is DQ32-39, sixth byte is DQ40-47, seventh byte is DQ48-55 and the eighth byte is DQ56-64.
Various	Vcc	Supply	Core power supply: +3.3V -5%/+10%
Various	Vss	Ground	Ground


SYNCHRONOUS ONLY - TRUTH TABLE

Operation	E1\	E2\	E3\	E4\	GW\	G\	CLK	DQ
Synchronous Write-Bank 1	L	H	H	H	L	H	↑	High-Z
Synchronous Read-Bank 1	L	H	H	H	H	L	↑	
Synchronous Write-Bank 2	H	L	H	H	L	H	↑	High-Z
Synchronous Read-Bank 2	H	L	H	H	H	L	↑	
Synchronous Write-Bank 3	H	H	L	H	L	H	↑	High-Z
Synchronous Read-Bank 3	H	H	L	H	H	L	↑	
Synchronous Write-Bank 4	H	H	H	L	L	H	↑	High-Z
Synchronous Read-Bank 4	H	H	H	L	H	L	↑	
Snooze Mode	X	X	X	X	X	X	X	High-Z

ABSOLUTE MAXIMUM RATINGS*

Voltage on Vcc Relative to Vss	-0.5V to +4.6V
Vin	-0.5V to Vcc +0.5V
Storage Temperature	-55°C to +125°C
Operating Temperature (Commercial)	0°C to +70°C
Operating Temperature (Industrial)	-40°C to +85°C
Short Circuit Output Current	20mA

*Stress greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions greater than those indicated in operational sections of this specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

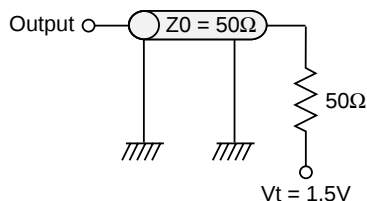
RECOMMENDED DC OPERATING CONDITIONS

Parameter	Sym	Min	Typ	Max	Units
Supply Voltage	Vcc	3.14	3.3	3.6	V
Supply Voltage	Vss	0.0	0.0	0.0	V
Input High	VIH	2.2	3.0	Vcc+0.3	V
Input Low	VIL	-0.3	0.0	0.8	V
Input Leakage	ILi	-2	1	2	mA
Output Leakage	ILO	-2	1	2	mA
Output High IOH = -4mA	VOH	2.4	-	-	V
Output Low IOL = 8mA	VOL	-	-	0.4	V

DC ELECTRICAL CHARACTERISTICS - READ CYCLE

Description	Symbol	Typ	9.5	10	Max 11	12	15	Units
Power Supply Current	Icc1	1.8	*	1.2	1.1	1.0	0.9	A
Power Supply Current Device Selected, No Operation	Icc	0.8	*	0.9	0.8	0.8	0.7	A
Snooze Mode	IccZZ	500	*	700	700	700	700	mA
CMOS Standby	Icc3	270	*	350	350	350	350	mA
Clock Running-Deselect	IccK	900	*	1.1	1.0	1.0	1.0	A

*TBD

AC TEST CIRCUIT


AC Output Load Equivalent

AC TEST CONDITIONS

Parameter	I/O	Unit
Input Pulse Levels	Vss to 3.0	V
Input and Output Timing Ref.	1.25	V
Output Test equivalencies	See figure, at left	


READ CYCLE TIMING PARAMETERS

Description	Symbol	9.5ns		10ns		11ns		12ns		15ns		Units
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Clock Cycle Time	t _{KHKH}	*	*	12		12		15		20		ns
Clock High Time	t _{KHKL}	*	*	5		5		5		6		ns
Clock Low Time	t _{KLKH}	*	*	5		5		5		6		ns
Clock to Output Valid	t _{KHQV}	*	*		10		11		12		15	ns
Clock to Output Invalid	t _{KHQX1}	*	*	3		3		3		3		ns
Clock to Output Low-Z	t _{KHQX}	*	*	2		2		2		2		ns
Output Enable to Output Valid	t _{GLQV}	*	*		5		5		5		6	ns
Output Enable to Output Low-Z	t _{GLQX}	*	*	0		0		0		0		ns
Output Enable to Output High-Z	t _{GHQZ}	*	*		5		5		5		6	ns
Address Setup	t _{AVKH}	*	*	2.5		2.5		2.5		2.5		ns
Bank Enable Setup	t _{EVKH}	*	*	2.5		2.5		2.5		2.5		ns
Address Hold	t _{KHAX}	*	*	1.0		1.0		1.0		1.0		ns
Bank Enable Hold	t _{KHEX}	*	*	1.0		1.0		1.0		1.0		ns

*TBD

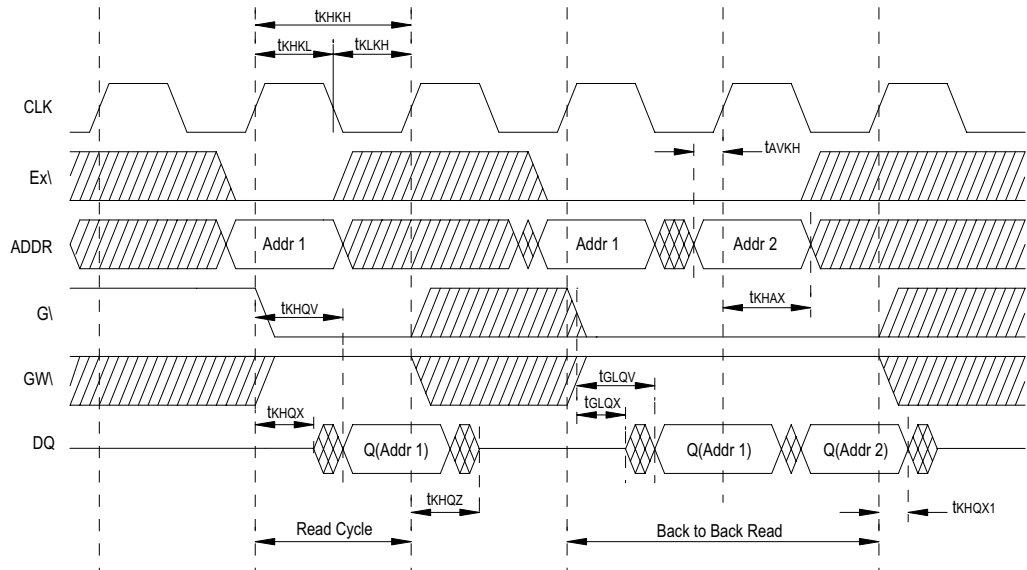
WRITE CYCLE TIMING PARAMETERS

Description	Symbol	9.5ns		10ns		11ns		12ns		15ns		Units
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Clock Cycle Time	t _{KHKH}	*	*	12		12		15		20		ns
Clock High Time	t _{KHKL}	*	*	5		5		5		6		ns
Clock Low Time	t _{KLKH}	*	*	5		5		5		6		ns
Address Setup	t _{AVKH}	*	*	2.5		2.5		2.5		2.5		ns
Address Hold	t _{KHAX}	*	*	1.0		1.0		1.0		1.0		ns
Bank Enable Setup	t _{EVKH}	*	*	2.5		2.5		2.5		2.5		ns
Bank Enable Hold	t _{KHEX}	*	*	1.0		1.0		1.0		1.0		ns
Global Write Enable Setup	t _{WVKH}	*	*	2.5		2.5		2.5		2.5		ns
Global Write Enable Hold	t _{KHWX}	*	*	1.0		1.0		1.0		1.0		ns
Data Setup	t _{DVKH}	*	*	2.5		2.5		2.5		2.5		ns
Data Hold	t _{KHDX}	*	*	1.0		1.0		1.0		1.0		ns

*TBD

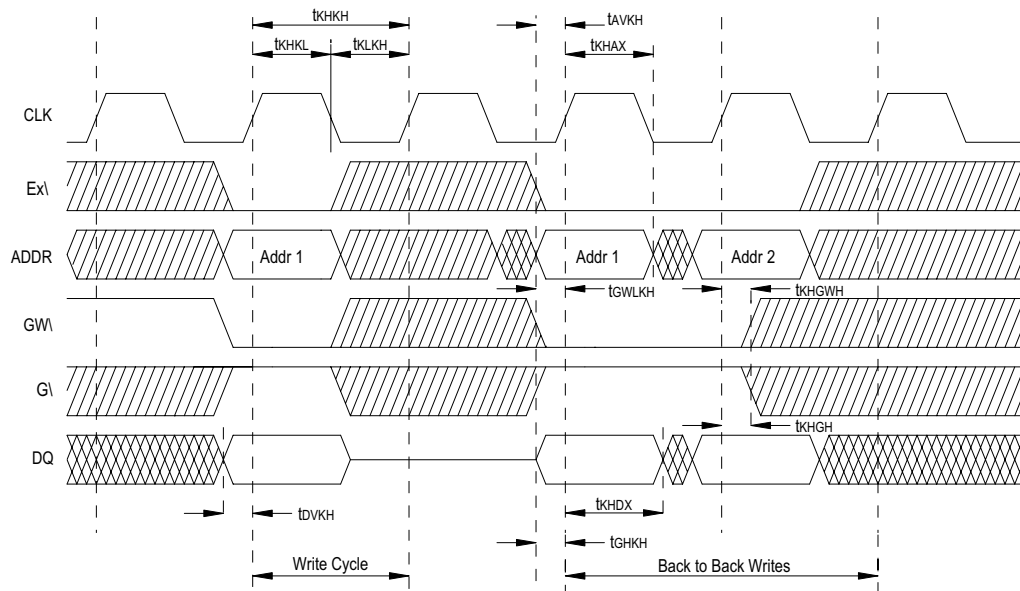


SYNCHRONOUS READ CYCLE

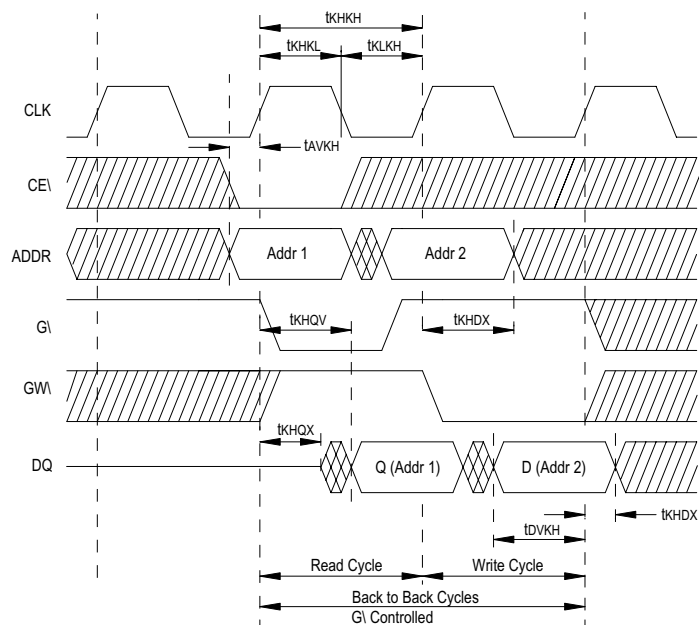




SYNCHRONOUS WRITE CYCLE

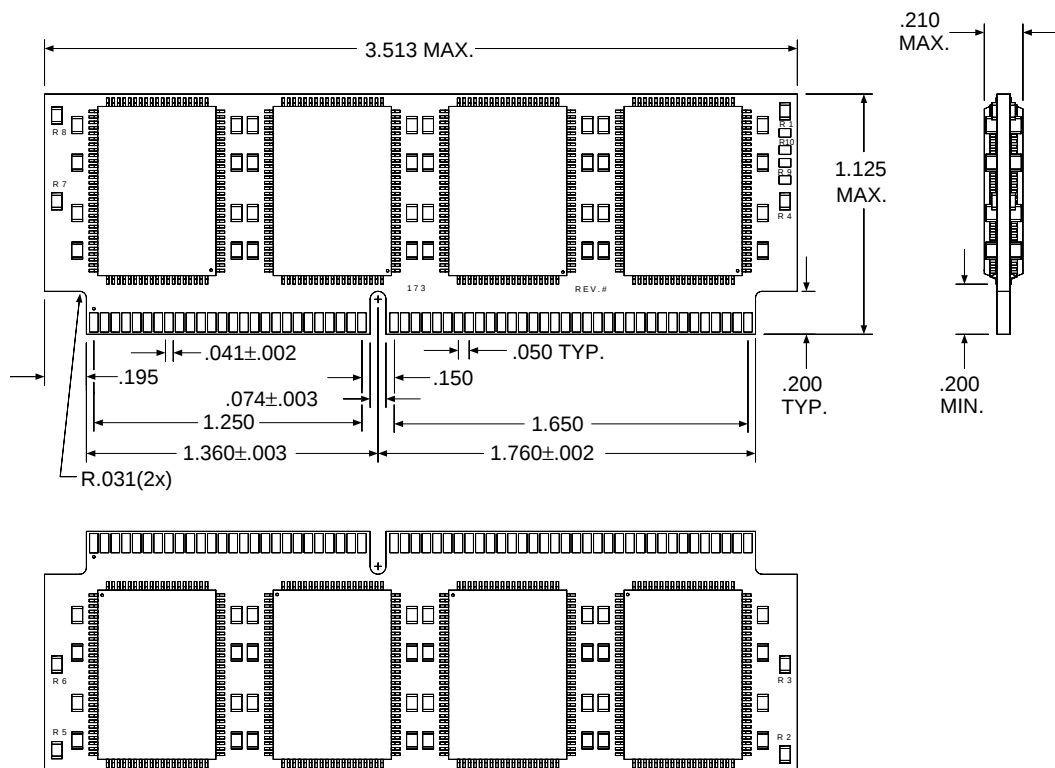


SYNCHRONOUS READ/WRITE CYCLE





PACKAGE DESCRIPTION 120 CARD EDGE DIMM



ORDERING INFORMATION

Part Number	Organization	Voltage	Speed (ns)	Package
EDI2GG46464V95D*	4x64Kx64	3.3	9.5	120 Card Edge DIMM
EDI2GG46464V10D	4x64Kx64	3.3	10	120 Card Edge DIMM
EDI2GG46464V11D	4x64Kx64	3.3	11	120 Card Edge DIMM
EDI2GG46464V12D	4x64Kx64	3.3	12	120 Card Edge DIMM
EDI2GG46464V15D	4x64Kx64	3.3	15	120 Card Edge DIMM

*Consult Factory for Availability